L Number	Hits	Search Text	DB	Time stamp
3	0	((nitrogen or "n.sub.2") near3 (atomic or radical or plasma) same (ammonia or "nh3" or "nh.sub.3")) same atmopshere and 117/$.ccls.	USPAT; US-PGPUB; EPO; DERWENT; IBM_TDB	2003/10/16 11:11
2	36	((nitrogen or "n.sub.2") near3 (atomic or radical or plasma) same (ammonia or "nh3" or "nh.sub.3")) and 117/$.ccls.	USPAT; US-PGPUB; EPO; DERWENT; IBM_TDB	2003/10/16 11:11
5	94	(nitrogen or "n.sub.2") near3 (atomic or radical or plasma) near20 (ammonia or "nh3" or "nh.sub.3") near20 (anneal$4 or rapid adj thermal or rta or heat near2 treat$)	USPAT; US-PGPUB; EPO; DERWENT; IBM_TDB	2003/10/16 11:37
9	107	sapphire near10 (silicon or si) near10 (sic or silicon adj carbide) near5 substrate same (gan or gallium adj nitride) and (gallium adj nitride or gan).ti.	USPAT; US-PGPUB; EPO; DERWENT; IBM_TDB	2003/10/16 11:39
10	4	(sapphire near10 (silicon or si) near10 (sic or silicon adj carbide) near5 substrate same (gan or gallium adj nitride) and (gallium adj nitride or gan).ti.) and 117/1-83.ccls.	USPAT; US-PGPUB; EPO; DERWENT; IBM_TDB	2003/10/16 14:07
12	91	(zno or zinc adj oxide) near10 solution same (anneal$ or rta or rapid adj thermal or heat adj treat$)	USPAT; US-PGPUB; EPO; DERWENT; IBM_TDB	2003/10/16 14:09
13	12	(zno or zinc adj oxide) near10 solution same (anneal$ or rta or rapid adj thermal or heat adj treat$) same crystal$	USPAT; US-PGPUB; EPO; DERWENT; IBM_TDB	2003/10/16 14:10
-	15	((ammonia or "nh.sub.3") same reducing near2 (gas$3 or vapor) same (heat adj treat$4 or anneal$4 or rapid adj thermal or rta or ptp or rtp)) and 438/$4.ccls.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/10/16 13:19
-	48	(nitrogen or "n.sub.2") near3 (atomic or radical or plasma) same reduc$4 near3 (gas$3 or atmosphere or vapor) and semiconductor	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/10/16 15:28
-	44	(nitrogen or "n.sub.2") near3 (atomic or radical or plasma) same reduc$4 near3 (gas$3 or atmosphere or vapor) and nitride	USPAT; US-PGPUB; EPO; DERWENT; IBM_TDB	2003/10/16 11:10
-	19	buffer same (spin near3 coat$4 or spin$1coat$4) same (GaN or "iii-v" or zno or zinc adj oxide or nitride)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/03/26 13:53
-	10	(spin near3 coat$4 or spin$1coat$4) near20 (GaN or "iii-v" or zno or zinc adj oxide or nitride) and MOCVD	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/03/26 13:55
-	2	(spin near3 coat$4 or spin$1coat$4) near20 MOCVD same nitride	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/03/26 13:55
-	62	(spin near3 coat$4 or spin$1coat$4) near20 MOCVD	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/03/26 13:59

C:\APPS\east\workspaces\09904129F.wsp

BEST AVAILABLE COPY

-	2	((spin near3 coat$4 or spin$1coat$4) near20 MOCVD) and ("iii-v" or gallium adj nitride or gan)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/03/26 14:02
-	14	spin near4 coat$4 near20 buffer and (gan or gallium adj nitride or "iii-v")	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/04/01 13:59
-	14	spin near4 coat$4 near20 (gan or gallium adj nitride or "iii-v")	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/04/01 14:02
-	24	spin near4 coat$4 near20 (zno or zinc adj oxide)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/04/01 14:03
-	36	p$1n near2 junction near10 (gan or gallium adj nitride) same buffer	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/10/15 17:30

C:\APPS\east\workspaces\09904129F.wsp